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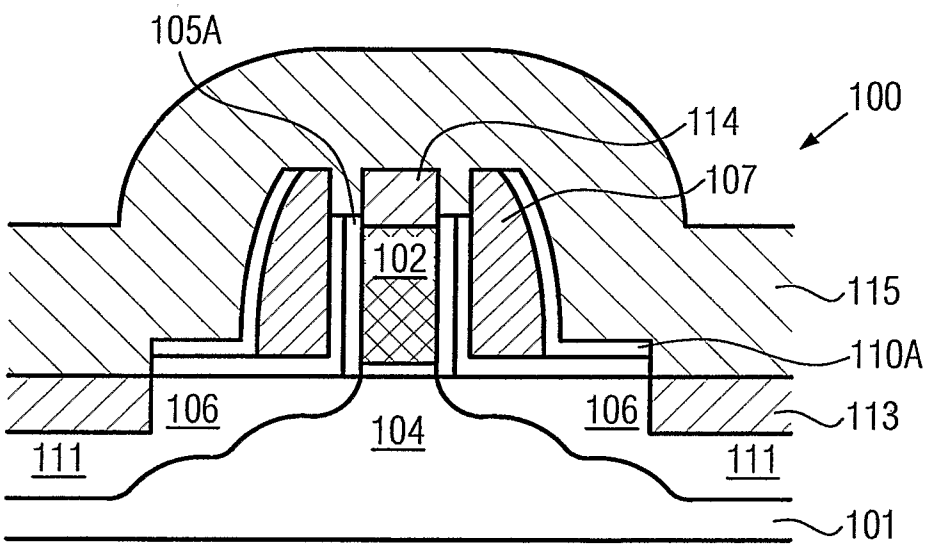
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(54) **Title:** TECHNIQUE FOR FORMING A CONTACT INSULATION LAYER WITH ENHANCED STRESS TRANSFER EFFICIENCY



(57) **Abstract:** By removing an outer spacer 109, used for the formation of highly complex lateral dopant profiles, prior to the formation of metal suicide, a high degree of process compatibility with conventional processes is obtained, while at the same time a contact liner layer 115 may be positioned more closely to the channel region, thereby allowing a highly efficient stress transfer mechanism for creating a corresponding strain in the channel region.

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